

*A1*

a pump radiation source with a radiation region for optically pumping the radiation generating quantum well structure, said pump radiation source including an edge-emitting semiconductor structure comprising a first waveguide layer and a second waveguide layer and an active layer between said first and second waveguide layers, said edge-emitting semiconductor structure being formed by the semi-conductor layer sequence being epitaxially and successively grown on the common substrate.

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Amend claim 16 as follows:

*A2*

16. An optically pumped surface-emitting semiconductor laser device according to claim 1, wherein the edge-emitting semiconductor structure includes an active layer embedded between said first waveguide layer and said second waveguide layer, said first wave guide layer and said second waveguide layer being embedded between a first cladding layer and a second cladding layer.

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Amend claim 20 as follows:

*A3*

20. An optically pumped surface-emitting semiconductor laser device according to claim 19, wherein:

the edge-emitting semiconductor structure includes said first waveguide layer and said second waveguide layer and an active layer, said active layer arranged between the first waveguide layer and the second waveguide layer; and

the quantum well structure being epitaxially grown on the second waveguide layer, covers only a sub-region of the edge-emitting semiconductor structure and is being optically coupled thereto, so that a part of the pump radiation generated in the edge-emitting semiconductor structure is being guided into the quantum well structure.

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